

NextPower 100 V, 9 m $\Omega$  N-channel MOSFET in LFPAK56 package

1 November 2017

Product data sheet

### 1. General description

NextPower 100 V standard level gate drive MOSFET. Qualified to 175 °C and recommended for industrial & consumer applications.

### 2. Features and benefits

- Low Q<sub>rr</sub> for higher efficiency and lower spiking
- Qualified to 175 °C
- Low Q<sub>G</sub> x R<sub>DSon</sub> FOM for high efficiency switching applications
- Strong avalanche energy rating (E<sub>as</sub>)
- Avalanche rated and 100% tested
- Ha-free and RoHS compliant LFPAK56 package
- Wave-solderable LFPAK56 package

### 3. Applications

- Synchronous rectifier in AC-DC and DC-DC
- BLDC motor control
- USB-PD and mobile fast-charge adapters
- LED lighting
- Full-bridge and half-bridge applications
- Flyback and resonant topologies

### 4. Quick reference data

Table 1. Qui	ck reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C	-	-	100	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	-	-	90	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>	-	-	198	W
Tj	junction temperature		-55	-	175	°C
Static chara	acteristics	·	· ·			
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 10	-	7.2	9	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 100 °C; Fig. 11	-	10.7	14	mΩ
Dynamic ch	naracteristics	·				
Q <sub>GD</sub>	gate-drain charge	$I_D$ = 25 A; $V_{DS}$ = 50 V; $V_{GS}$ = 10 V;	-	7.5	-	nC
Q <sub>G(tot)</sub>	total gate charge	Fig. 12; Fig. 13	-	38.5	-	nC

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Symbol	Parameter	Conditions		Min	Тур	Мах	Unit	
Avalanche ruggedness								
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$ \begin{array}{l} {\sf I}_{D} = 30.3 \; {\sf A}; \; {\sf V}_{sup} \leq \; 100 \; {\sf V}; \; {\sf R}_{GS} = 50 \; \Omega; \\ {\sf V}_{GS} = 10 \; {\sf V}; \; {\sf T}_{j(init)} = 25 \; {\rm ^{\circ}C}; \; \underline{{\sf Fig. 4}}; \\ {\sf Unclamped} \end{array} $	[1]	-	-	234	mJ	
Source-drain diode								
Q <sub>r</sub>	recovered charge	$I_{S} = 25 \text{ A}; \text{ d}I_{S}/\text{d}t = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V}; \\ \text{V}_{DS} = 50 \text{ V}; \frac{\text{Fig. 16}}{16}$		-	52.6	-	nC	

[1] Protected by 100% test

### 5. Pinning information

#### Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source	ل <del>ا دے ب</del> ا	
3	S	source	a	G
4	G	gate		mbb076 S
mb	D	mounting base; connected to drain	ī 2 3 4 LFPAK56; Power- SO8 (SOT669)	

### 6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
PSMN8R7-100YSF	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669			

### 7. Marking

Table 4. Marking codes	
Type number	Marking code
PSMN8R7-100YSF	8F7S10

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### 8. Limiting values

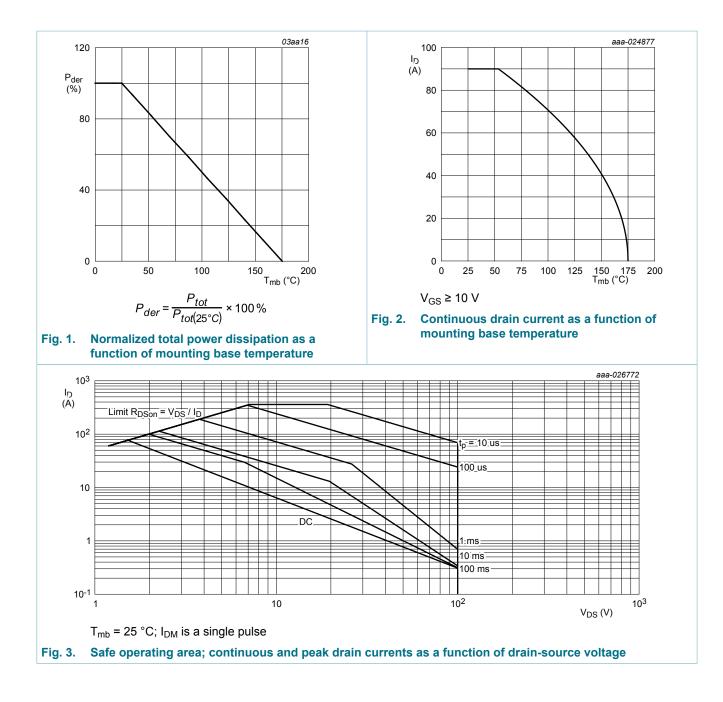
#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤  T <sub>j</sub> ≤  175 °C		-	100	V
V <sub>DGR</sub>	drain-gate voltage	25 °C ≤ $T_j$ ≤ 175 °C; $R_{GS}$ = 20 kΩ		-	100	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	198	W
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	90	А
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <u>Fig. 2</u>		-	71	А
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$ ; Fig. 3		-	360	А
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature			-	260	°C
Source-drain	n diode					
Is	source current	T <sub>mb</sub> = 25 °C		-	90	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	360	А
Avalanche r	uggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$ \begin{array}{l} I_{D} = 30.3 \; \text{A}; \; V_{sup} \leq \; 100 \; \text{V}; \; \text{R}_{GS} = 50 \; \Omega; \\ V_{GS} = 10 \; \text{V}; \; \text{T}_{j(\text{init})} = 25 \; ^{\circ}\text{C}; \; \overline{\text{Fig. 4}}; \\ \text{Unclamped} \end{array} $	[1]	-	234	mJ
I <sub>AS</sub>	non-repetitive avalanche current	$V_{sup} \le 100 \text{ V}; V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \text{ °C}; R_{GS} = 50 \Omega$	[1]	-	30.3	А

[1] Protected by 100% test

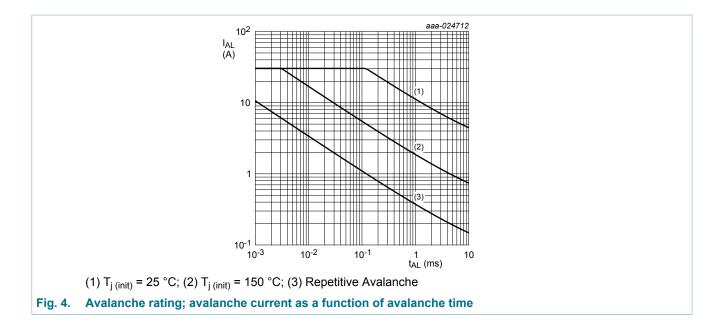
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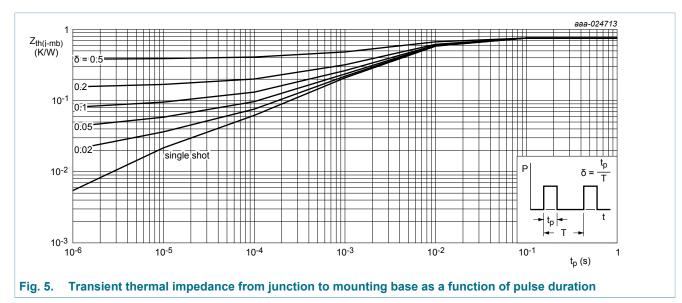
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### 9. Thermal characteristics

#### Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	0.67	0.76	K/W



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### **10. Characteristics**

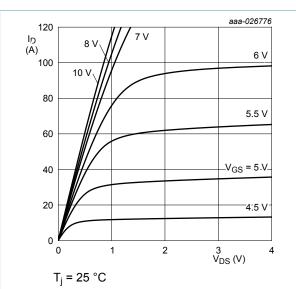
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static charac	teristics					
V <sub>(BR)DSS</sub>	drain-source	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	100	-	-	V
	breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -55 °C	90	-	-	V
V <sub>GS(th)</sub>	gate-source threshold	I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = -55 °C	-	3.6	-	V
	voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = 175 °C	-	1.9	-	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	2	3.1	4	V
$\Delta V_{GS(th)} / \Delta T$	gate-source threshold voltage variation with temperature	25 °C ≤ T <sub>j</sub> ≤ 175 °C	-	-8	-	mV/K
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 100 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.02	5	μA
		V <sub>DS</sub> = 100 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 125 °C	-	-	100	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	5	100	nA
		V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	5	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	7.2	9	mΩ
		$V_{GS}$ = 7 V; I <sub>D</sub> = 20 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	8.2	13.2	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 100 °C; <u>Fig. 11</u>	-	10.7	14	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; <u>Fig. 11</u>	-	15.8	19.8	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz	-	0.8	-	Ω
Dynamic cha	racteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$ Fig. 12; Fig. 13	-	38.5	-	nC
		$I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V$	-	19.8	-	nC
Q <sub>GS</sub>	gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$	-	12.8	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate- source charge	Fig. 12; Fig. 13	-	7.7	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate- source charge		-	5.1	-	nC
Q <sub>GD</sub>	gate-drain charge		-	7.5	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V; <u>Fig. 12</u> ; <u>Fig. 13</u>	-	4.9	-	V
C <sub>iss</sub>	input capacitance	$V_{DS}$ = 50 V; $V_{GS}$ = 0 V; f = 1 MHz;	-	2758	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 14</u>	-	532	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	17	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 50 \text{ V}; \text{ R}_{L} = 2 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	12.5	-	ns
t <sub>r</sub>	rise time	R <sub>G(ext)</sub> = 5 Ω; T <sub>j</sub> = 25 °C	-	11	-	ns

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
t <sub>d(off)</sub>	turn-off delay time			-	22.5	-	ns
t <sub>f</sub>	fall time			-	12.7	-	ns
Source-drain diode							
V <sub>SD</sub>	source-drain voltage	$I_{S}$ = 25 A; $V_{GS}$ = 0 V; $T_{j}$ = 25 °C; <u>Fig. 15</u>		-	0.8	1.2	V
t <sub>rr</sub>	reverse recovery time	I <sub>S</sub> = 25 A; dI <sub>S</sub> /dt = -100 A/μs; V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 50 V; <u>Fig. 16</u>		-	45.5	-	ns
Qr	recovered charge			-	52.6	-	nC



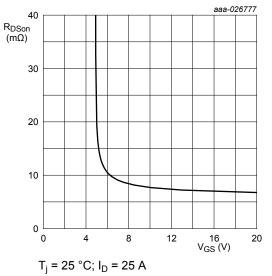
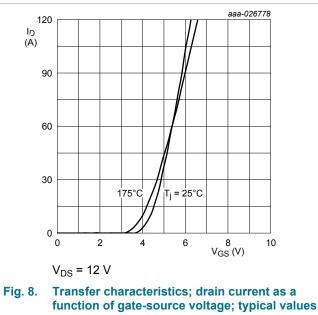
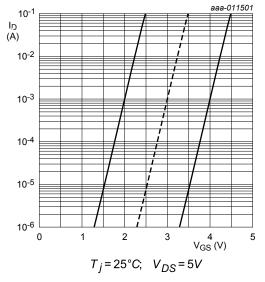


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values



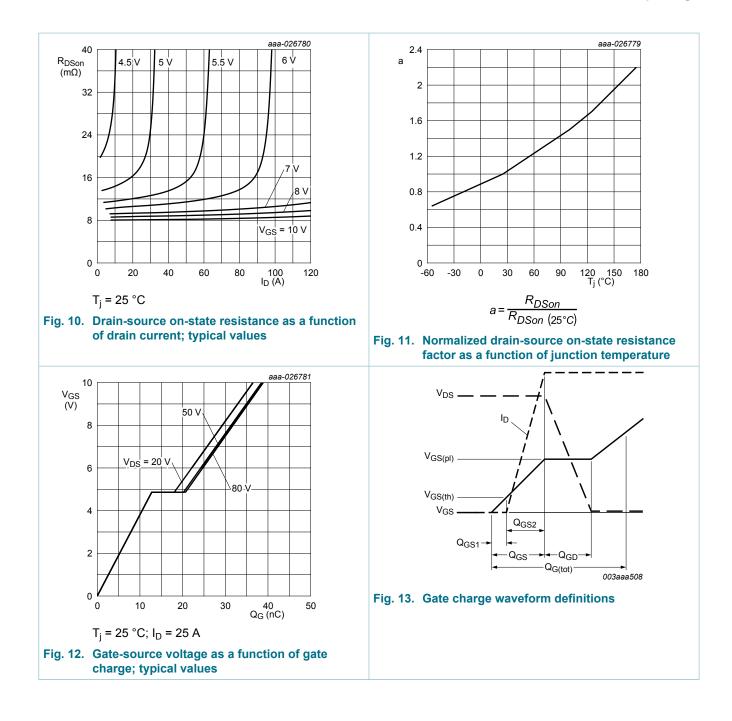




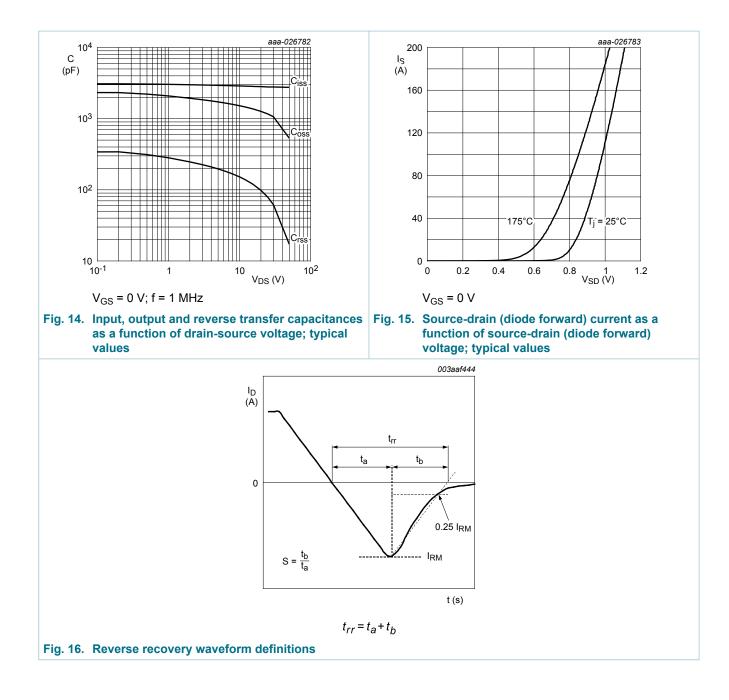


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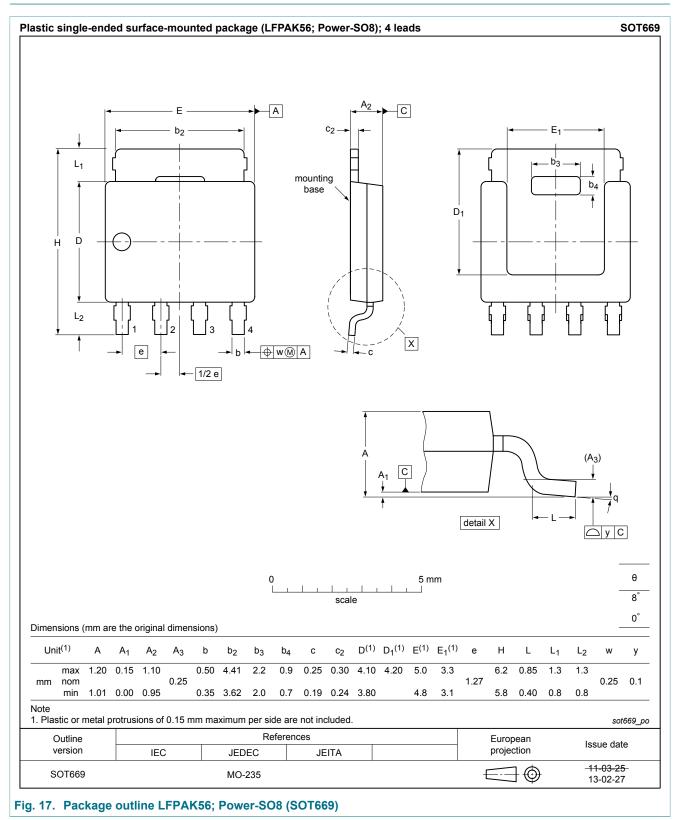


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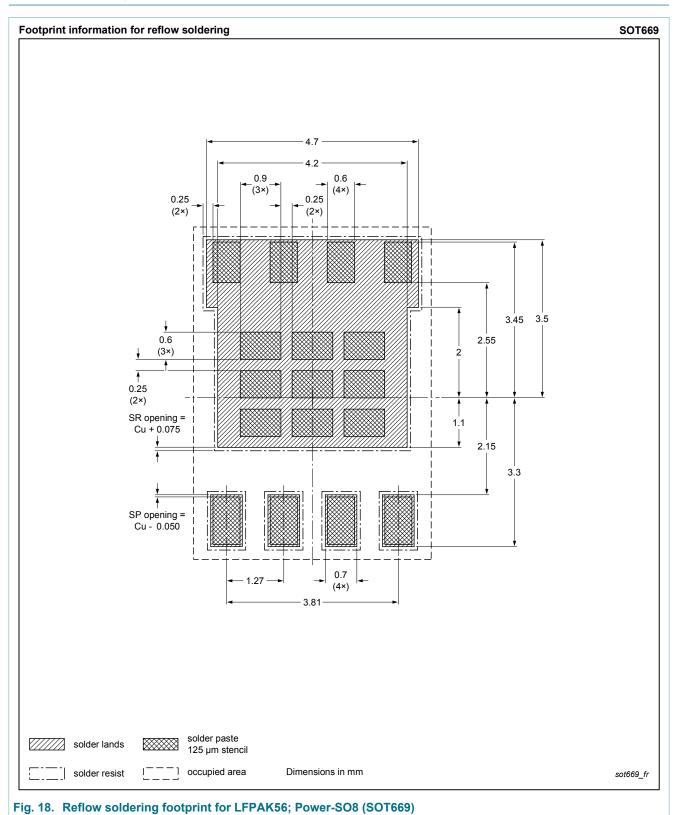
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### 11. Package outline



#### NextPower 100 V, 9 mΩ N-channel MOSFET in LFPAK56 package

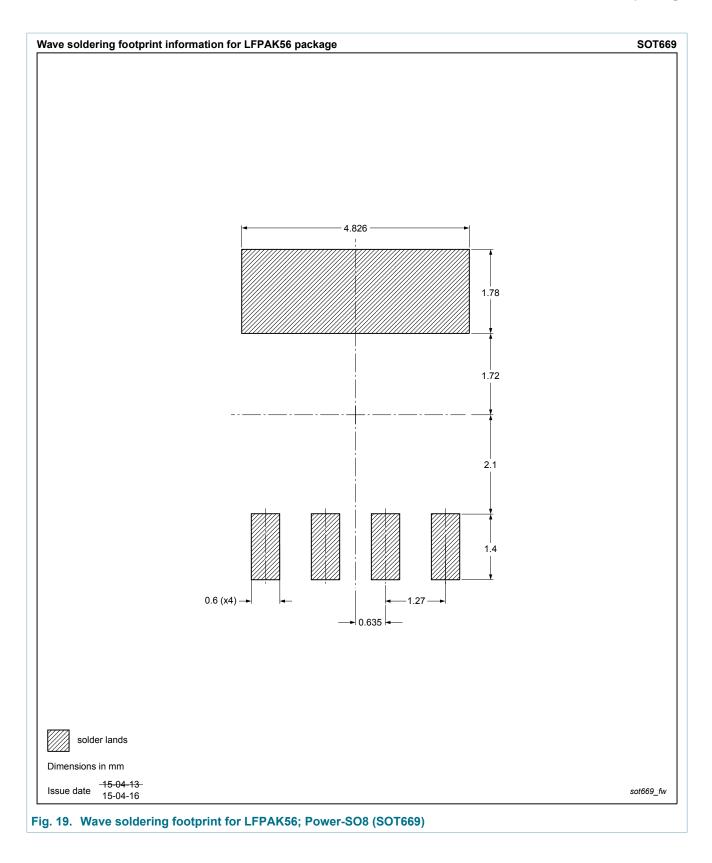
### 12. Soldering



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### 13. Legal information

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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